NPN SILICON HIGH FREQUENCY TRANSISTOR

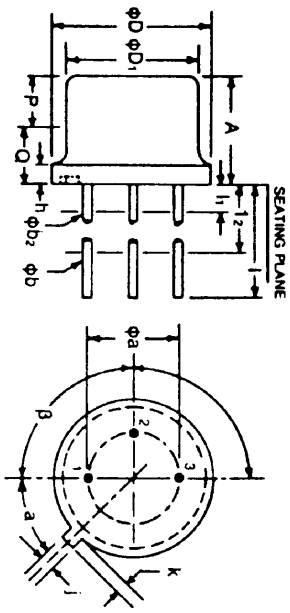
DESCRIPTION:

The **2SC2592** is a High Frequency Transistor Designed for General Purpose VHF-UHF Amplifier Applications.

MAXIMUM RATINGS

I_C	250 mA
V_{CE}	30 V
P_{DISS}	3.5 W @ T_C = 25 ^{O}C
T_J	-65 to +200 ^{O}C
T_{STG}	-65 to +200 ^{O}C
θ_{JC}	50 ^{O}C/W

PACKAGE STYLE TO-39



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
Φa	0.190	0.210	4.83	5.33
A	0.240	0.260	6.10	6.60
Φb	0.016	0.021	0.406	0.533
Φb2	0.016	0.019	0.406	0.483
ΦD	0.350	0.370	8.89	9.40
ΦD1	0.315	0.335	8.00	8.51
h	0.009	0.125	0.229	3.18
j	0.028	0.034	0.711	0.864
k	0.029	0.040	0.737	1.02
l	0.500		12.70	
l1		0.050		1.27
l2	0.250		6.35	
P	0.100		2.54	
Q				
a	45° NOMINAL			
β	90° NOMINAL			

1 = Emitter 2 = Base
3 & 4 = Collector (Case)

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 1.0 mA			20			V
BV_{CBO}	I_C = 100 µA			30			V
BV_{EBO}	I_E = 100 µA			3			V
I_{CBO}	V_{CB} = 20 V					10	µA
h_{FE}	V_{CE} = 10 V	I_C = 80 mA		30	80	200	---
f_t	V_{CE} = 10 V	I_E = 60 mA	f = 200 MHz	2800	3300		MHz
C_{CB}	V_{CB} = 10 V		f = 1.0 MHz			2.5	pF
$\|S21E\|^2$	V_{CE} = 10 V	I_E = 60 mA	f = 500 MHz	8.5			dB
NF	V_{CE} = 10 V	I_C = 10 mA V	f = 500 MHz		3.5		dB

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Specifications are subject to change without notice.

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